

Amendments to Claims

Claims 1-9 (cancelled).

5 10. (Previously Amended) A method of creating a substrate having multiple regions for creating low-voltage transistors of a first and second conductivity and high-voltage transistors of a first conductivity, consisting essentially of the steps of:

10 creating a defined deposition of a first dielectric layer to expose a first region and a second region;

implanting a first conductivity dopant into the first and second regions;

applying a first protective coating over the first and second regions;

driving in the first conductivity dopant into the substrate;

removing the first dielectric layer;

15 creating a defined deposition of a second dielectric layer in the same location as the defined deposition of the first dielectric layer;

implanting a second conductivity dopant in the substrate disposed under the defined deposition of the second dielectric layer;

driving in the second conductivity dopant into the substrate;

20 removing the first protective coating and the second dielectric layer;

creating a patterned third dielectric layer over the surface of the substrate to expose the drain and source of the first and second conductivity low-voltage transistors and the first conductivity high-voltage transistor;

25 creating a defined deposition of a fourth dielectric layer disposed on the drain and source of the first conductivity low-voltage transistor;

applying a second protective coating over the first and second regions;

implanting a second conductivity dopant into the substrate disposed under the drain and source of the first conductivity low-voltage transistor;

removing the second protective coating;

30 creating a fifth dielectric layer in areas of the substrate where the third dielectric layer is not located;

removing the patterned third dielectric layer; and  
then further comprising the steps of:

creating a sixth dielectric layer over the surface of the substrate to form a gate oxide;

depositing a gate material over the sixth dielectric layer; and

patterning the sixth dielectric layer and the gate material to define gate

5 regions of the first and second low conductivity transistors and a gate region of the first conductivity high-voltage transistor.

Claim 11 (cancelled).

10 12. (Previously Amended) A method of creating an integrated circuit having a second conductivity type low-voltage transistor in a first region, a first conductivity type high-voltage transistor in a second region, and a first conductivity low-voltage transistor in a third region, comprising the steps of:

doping the first and second regions with a first dopant concentration to both  
15 control the threshold voltage of the second conductivity type low-voltage transistor and set a breakdown voltage of the first conductivity high-voltage transistor; and

doping the third region with a second dopant concentration to control the threshold voltage of the first conductivity type low-voltage transistor;

wherein an additional voltage threshold adjust implant step to adjust the  
20 threshold voltages of the first and second low-voltage transistors is not performed.

Claim 13 (cancelled).

14. (Currently Amended) A method of processing an integrated circuit having a  
25 second conductivity type low-voltage transistor in a first region, a first conductivity high-voltage transistor in a ~~third~~second region, and a first conductivity low-voltage type transistor in a ~~second~~third region, comprising the steps of:

doping the first and second regions with a first dopant concentration  
thereby determining a threshold voltage of the second conductivity type low-  
30 voltage transistor and a breakdown voltage of the first conductivity type high-voltage transistor; and

doping the third region with a second dopant concentration; and  
excluding the step of:

implanting an additional threshold voltage adjustment of the first and second low-voltage transistors; and

wherein the first and second regions have the substantially the same dopant concentration after processing of the integrated circuit.

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Claim 15 (cancelled).

16. (Original) A method of creating a substrate having multiple regions for creating low-voltage transistors of a first and second conductivity and high-voltage transistors of a first conductivity, comprising the steps of:

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creating a defined deposition of a first dielectric layer to expose a first region and a second region; then

implanting a first conductivity dopant into the first and second regions; then applying a first protective coating over the first and second regions; then

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driving in the first conductivity dopant into the substrate; then

removing the first dielectric layer; then

creating a defined deposition of a second dielectric layer in the same location as the defined deposition of the first dielectric layer; then

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implanting a second conductivity dopant in the substrate disposed under the defined deposition of the second dielectric layer; then

driving in the second conductivity dopant into the substrate; then

removing the first protective coating and the second dielectric layer; then

creating a patterned third dielectric layer over the surface of the substrate to expose the drain and source of the first and second conductivity low-voltage

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transistors and the first conductivity high-voltage transistor; then

creating a defined deposition of a fourth dielectric layer disposed on the drain and source of the first conductivity low-voltage transistor; then

applying a second protective coating over the first and second regions;

then

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implanting a second conductivity dopant into the substrate disposed under the drain and source of the first conductivity low-voltage transistor; then

removing the second protective coating; then

creating a fifth dielectric layer in areas of the substrate where the third dielectric layer is not located; then

removing the patterned third dielectric layer;  
creating a sixth dielectric layer over the surface of the substrate to form a  
gate oxide;  
depositing a gate material over the sixth dielectric layer; and  
5        patterning the sixth dielectric layer and the gate material to define gate  
regions of the first and second low conductivity transistors and a gate region of the  
first conductivity high-voltage transistor.

Claim 17 (cancelled).

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